

ABSTRACT

A semiconductor device includes a first active fin having first fin-type patterns and a first separation region therebetween; a second active fin having second fin-type patterns and a second separation region therebetween, where a first trench region between the first and second active fins has a first depth, and the first and second fin-type patterns are merged by the first trench region; a third active fin adjacent to the first active fin, where a second trench region between the first and third active fins has a second depth that is greater than the first depth; and at least one first gate line intersecting the first and second active fins and the third active fins.

FIG. 1